/ Descriptions

TO-263 PNP

Silicon PNP transistor in a TO-263 Plastic Package.

/ Features

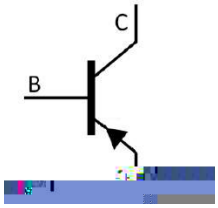
BRMJB41CQ AEC-Q101

Complement to BRMJB41CQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

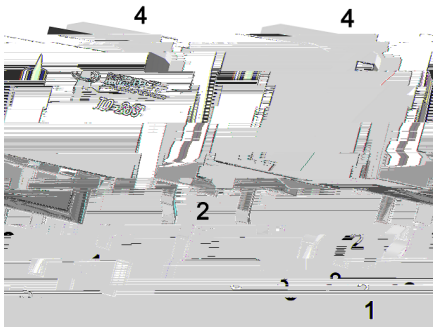
/ Applications

Medium power linear switching applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 4 Collector PIN 3 Emitter

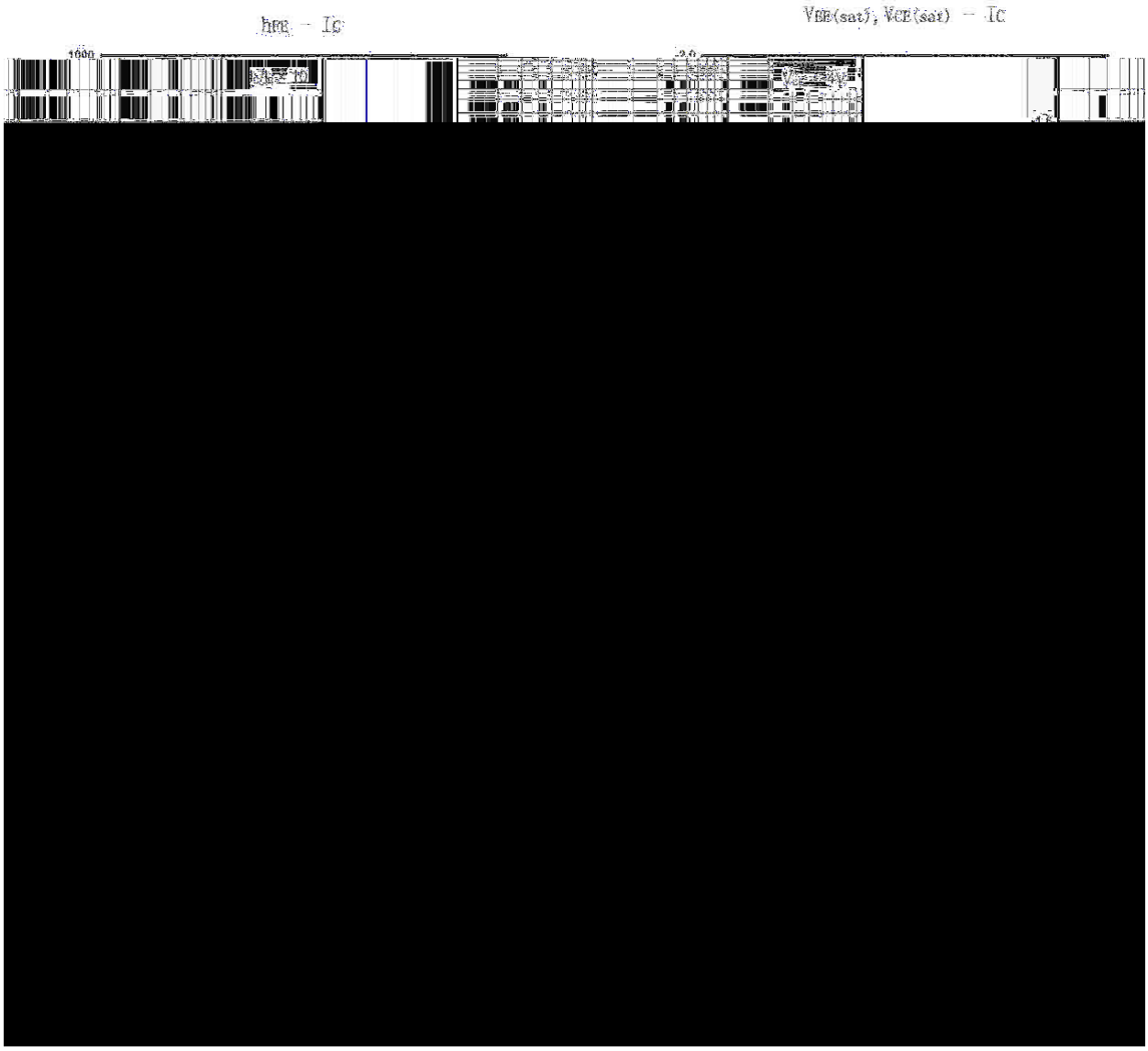
/ h_{FE} Classifications & Marking

See Marking Instructions.

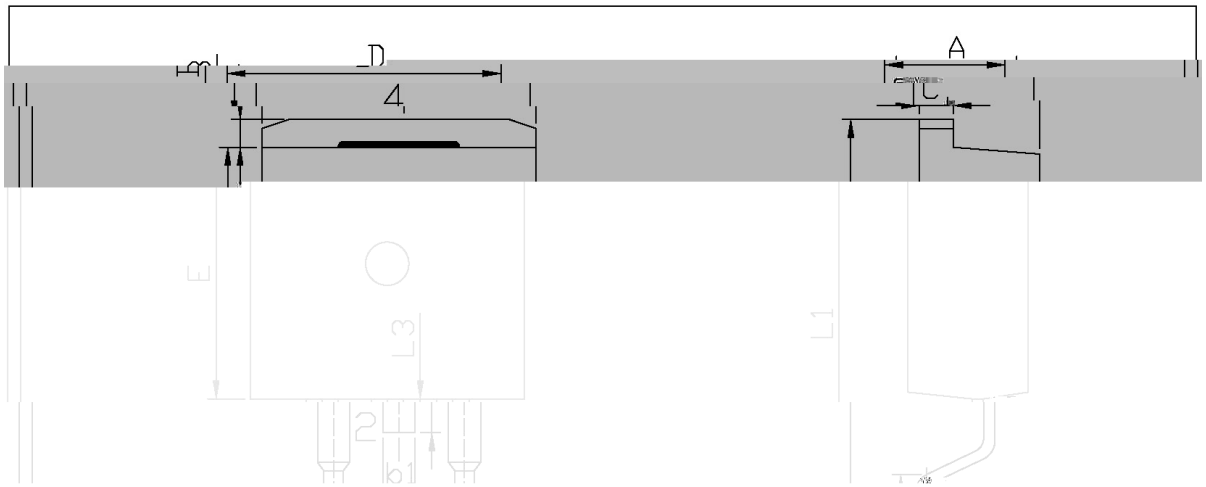
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Peak Collector Current	I_{CP}	-10	A
Base Current - Continuous	I_B	-2.0	A
Power Dissipation	P_D	2.0	W
Power Dissipation	P_D(Tc=25)	65	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{sag}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-30mA I_B=0	-100			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=-60V I_B=0			-0.7	mA

/ Electrical Characteristic Curve



/ Package Dimensions



	Max		Min	Max		Min
	9.40	A	4.30	4.70	E	9.00
	2.74	B	1.00	1.40	e1	2.34
5.00	16.00	b1	1.15	1.35	L1	
2.24	2.84	b2			L2	
1.20	1.60	C	1.20	1.40	L3	
		D	9.80	10.20		

( ) /

[redacted]

Note:

1	150 200	60 120sec;	1.Preheating:150~200	, Time:60~120sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5	, Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

[redacted]

/ REEL

CU3 Tm03 B03 T1215